



STPS20H100CT/CF/CG/CR/CFP

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

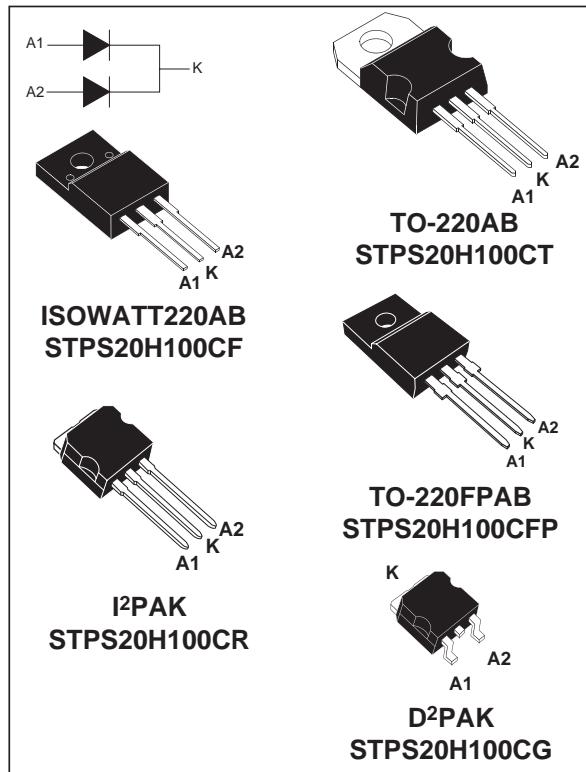
I _{F(AV)}	2 x 10 A
V _{RRM}	100 V
T _j	175°C
V _F (max)	0.64 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- HIGH JUNCTION TEMPERATURE CAPABILITY
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW LEAKAGE CURRENT
- AVALANCHE RATED
- INSULATED PACKAGE: ISOWATT220AB, TO-220FPAB
Insulating Voltage = 2000V DC
Capacitance = 45 pF
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap schottky rectifier designed for high frequency miniature Switched Mode Power Supplies such as adaptors and on board DC/DC converters.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V _{RRM}	Repetitive peak reverse voltage				100	V
I _{F(RMS)}	RMS forward current				30	A
I _{F(AV)}	Average forward current $\delta = 0.5$	TO-220AB	T _c = 160°C	per diode per device	10	A
		D ² PAK / I ² PAK			20	
I _{FSM}	Surge non repetitive forward current	ISOWATT220AB	T _c = 145°C		250	A
					1	A
I _{IRRM}	Repetitive peak reverse current	TO-220FPAB			3	A
I _{IRSM}	Non repetitive peak reverse current				10800	W
P _{ARM}	Repetitive peak avalanche power	tp = 1μs	T _j = 25°C		- 65 to + 175	°C
T _{stg}	Storage temperature range					
T _j	Maximum operating junction temperature *				175	°C
dV/dt	Critical rate of rise of reverse voltage				10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / D ² PAK / I ² PAK	Per diode	1.6	°C/W
		ISOWATT220AB / TO-220FPAB	Per diode	4	
		TO-220AB / D ² PAK / I ² PAK	Total	0.9	
		ISOWATT220AB / TO-220FPAB	Total	3.2	°C/W
$R_{th(c)}$		TO-220AB / D ² PAK / I ² PAK	Coupling	0.15	
		ISOWATT220AB / TO-220FPAB	Coupling	2.5	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			4.5	µA
		$T_j = 125^\circ\text{C}$			2	6	mA
V_F **	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8 \text{ A}$			0.71	V
		$T_j = 25^\circ\text{C}$	$I_F = 10 \text{ A}$			0.77	
		$T_j = 25^\circ\text{C}$	$I_F = 16 \text{ A}$			0.81	
		$T_j = 25^\circ\text{C}$	$I_F = 20 \text{ A}$			0.88	
		$T_j = 125^\circ\text{C}$	$I_F = 8 \text{ A}$		0.56	0.58	
		$T_j = 125^\circ\text{C}$	$I_F = 10 \text{ A}$		0.59	0.64	
		$T_j = 125^\circ\text{C}$	$I_F = 16 \text{ A}$		0.65	0.68	
		$T_j = 125^\circ\text{C}$	$I_F = 20 \text{ A}$		0.67	0.73	

Pulse test : * $t_p = 5 \text{ ms}, \delta < 2\%$

** $t_p = 380 \mu\text{s}, \delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.55 \times I_{F(AV)} + 0.009 \times I_F^2 (\text{RMS})$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

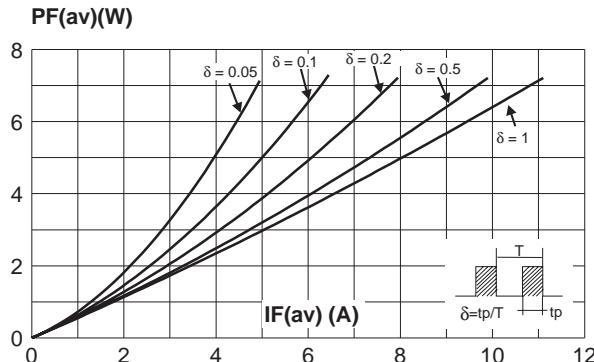


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

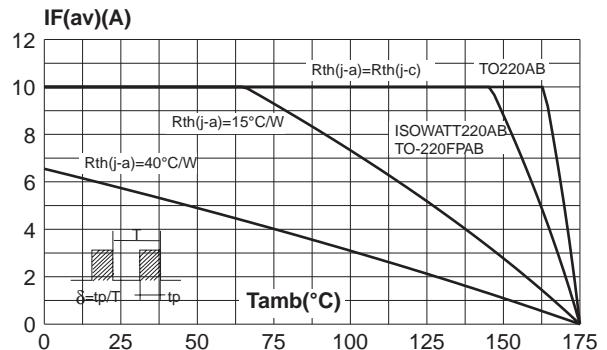


Fig. 3: Normalized avalanche power derating versus pulse duration.

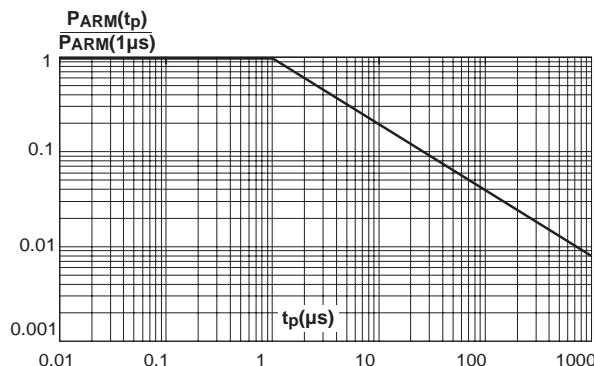


Fig. 4: Normalized avalanche power derating versus junction temperature.

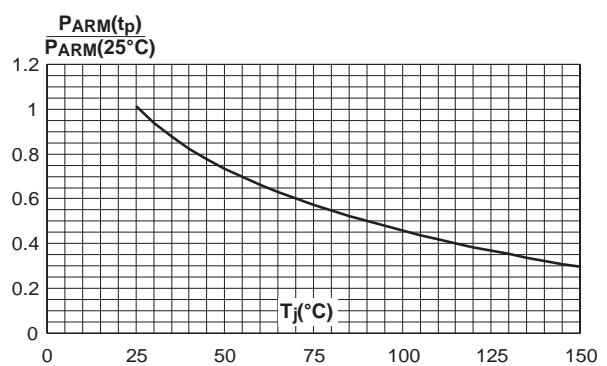


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (TO-220AB, D²PAK, I²PAK)

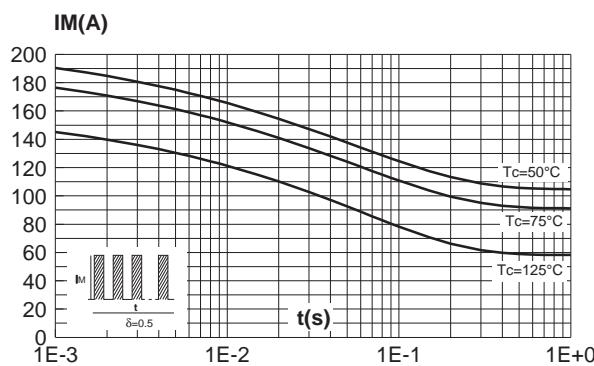
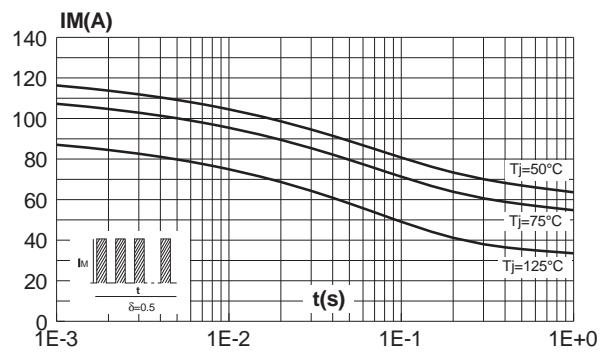


Fig. 6: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (ISOWATT220AB, TO-220FPAB).



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Fig. 7-1: Relative variation of thermal impedance junction to case versus pulse duration (per diode) (TO-220AB, D²PAK, I²PAK).

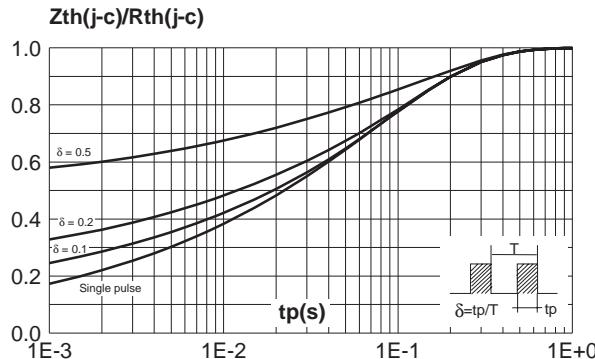


Fig. 7-2: Relative variation of thermal impedance junction to case versus pulse duration (per diode) (ISOWATT220AB, TO-220FPAB).

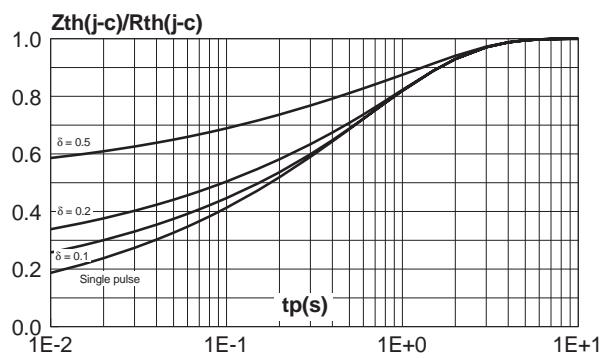


Fig. 8: Reverse leakage current versus reverse voltage applied (typical values, per diode).

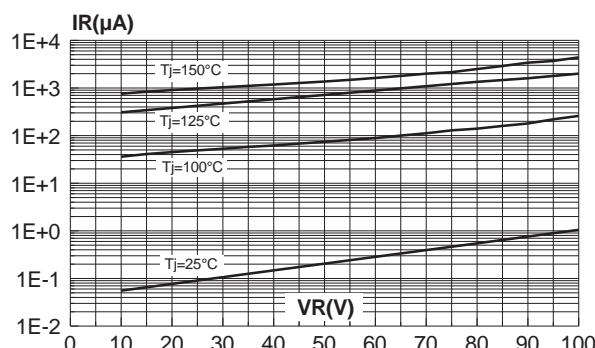


Fig. 9: Junction capacitance versus reverse voltage applied (typical values, per diode).

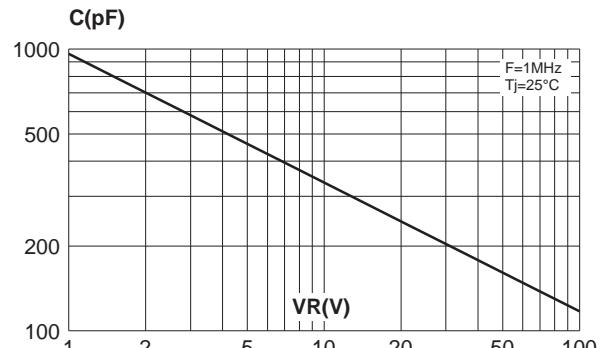


Fig. 10: Forward voltage drop versus forward current (maximum values, per diode).

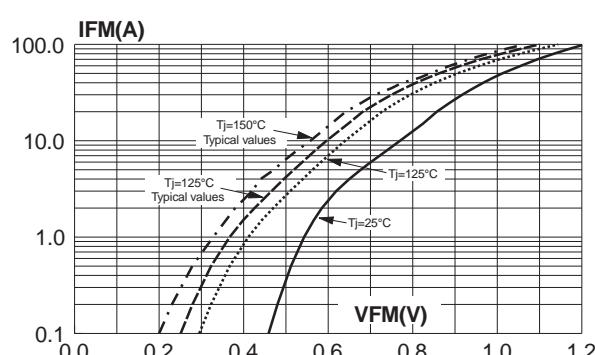
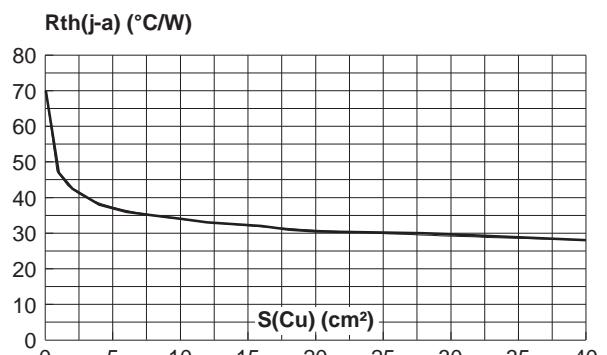


Fig. 11: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35µm) (D²PAK).



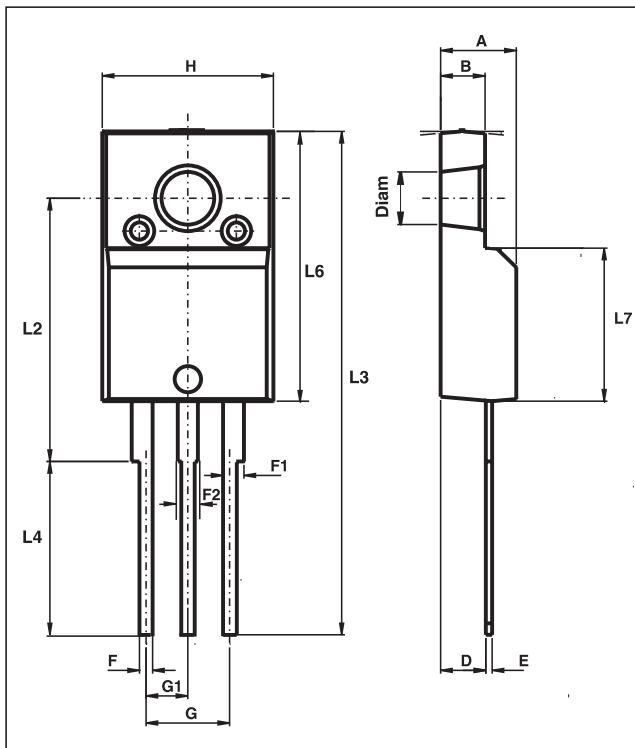
PACKAGE MECHANICAL DATA
TO-220AB

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

STPS20H100CT/CF/CG/CR/CFP

PACKAGE MECHANICAL DATA

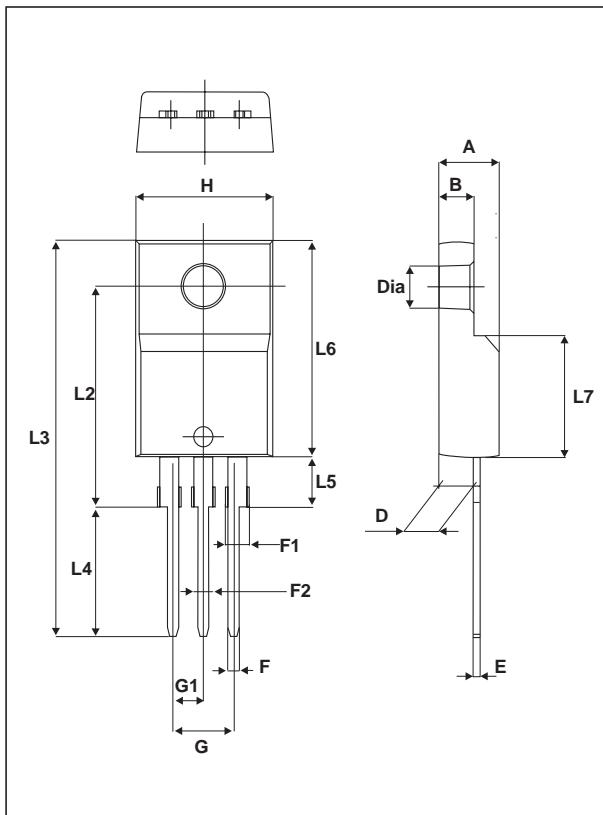
ISOWATT220AB



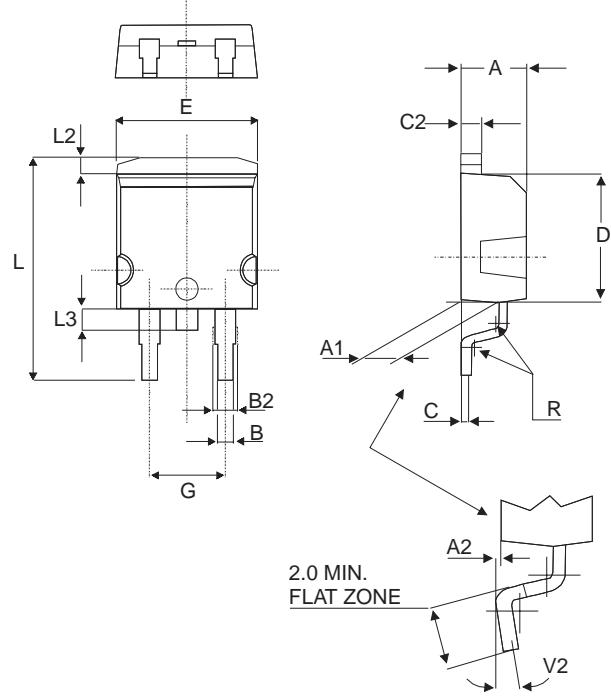
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	2.50	2.70	0.098	0.106
D	2.50	2.75	0.098	0.108
E	0.40	0.70	0.016	0.028
F	0.75	1.00	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.40	2.70	0.094	0.106
H	10.00	10.40	0.394	0.409
L2	16.00 typ.		0.630 typ.	
L3	28.60	30.60	1.125	1.205
L4	9.80	10.60	0.386	0.417
L6	15.90	16.40	0.626	0.646
L7	9.00	9.30	0.354	0.366
Diam	3.00	3.20	0.118	0.126

PACKAGE MECHANICAL DATA

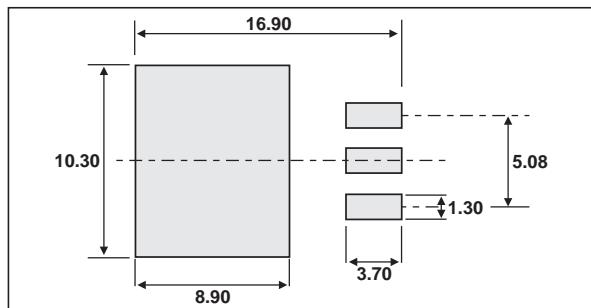
TO-220FPAB



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

PACKAGE MECHANICAL DATA
D²PAK


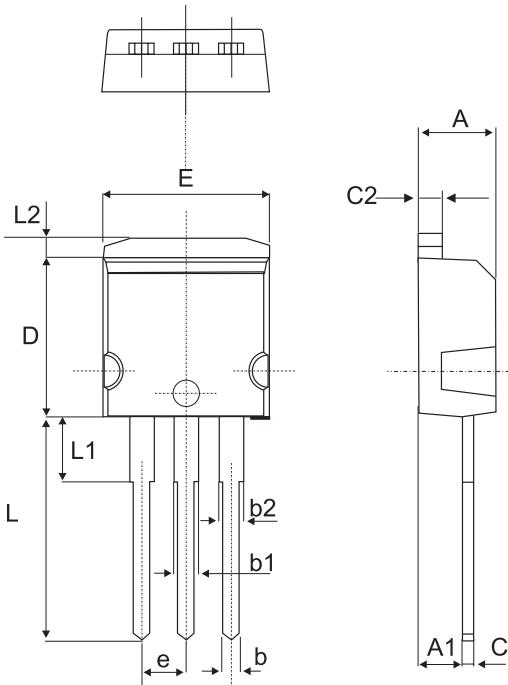
REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.049	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

FOOT PRINT DIMENSIONS (in millimeters)


STPS20H100CT/CF/CG/CR/CFP

PACKAGE MECHANICAL DATA

I²PAK



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
b	0.70		0.93	0.028		0.037
b1	1.20		1.38	0.047		0.054
b2	1.25	1.40		0.049	0.055	
C	0.45		0.60	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
e	2.44		2.64	0.096		0.104
E	10.00		10.28	0.394		0.405
L	13.10		13.60	0.516		0.535
L1	3.48		3.78	0.137		0.149
L2	1.27		1.40	0.050		0.055

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20H100CT	STPS20H100CT	TO-220AB	2.20g	50	Tube
STPS20H100CF	STPS20H100CF	ISOWATT220AB	2.08g	50	Tube
STPS20H100CFP	STPS20H100CFP	TO-220FPAB	2.0 g	50	Tube
STPS20H100CR	STPS20H100CR	I ² PAK	1.49g	50	Tube
STPS20H100CG	STPS20H100CG	D ² PAK	1.48g	50	Tube
STPS20H100CG-TR	STPS20H100CG	D ² PAK	1.48g	1000	Tape & reel

- Epoxy meets UL94,V0

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